

Atomistic Simulations as a Driver of Industrial Innovation

Ray Shan Materials Design

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Outline

- Industrial value of materials research
- The MedeA software of Materials Design
- Examples
 - Device optimization with Infineon
 - Battery research with **Toyota**
 - Gate-stack control with Texas Instruments
 - Ultrahard materials
 - Polymers and Fluids
- Conclusions



Value of Materials Research



A380

Creation of products which are

- Valuable for customer
- Innovative
- Safe and reliable
- Efficient to manufacture
- Environmentally responsible
- Meeting regulations



Value of Modeling and Simulation



- Prediction of properties
- Understanding mechanisms











Innovation Process



- Improvement of industrial products is a long-term iterative process
- Materials modeling and simulation are catalysts of this process





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MedeA Software Environment





Breadth of Applications



Automotive



Metals and Alloys



Aerospace



Glass and Ceramics





Batteries and Energy Storage



Oil & Gas



Minerals



Catalysts

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Electronics









Materials Properties from MedeA



Structural properties

- Molecular structures
- Crystal structures
- Surface structures
- Structure around defects
- Morphologies
- Adsorption geometries
- Structures of interfaces
- Liquids and amorphous systems

Thermo-Mechanical properties

- Density
- Elastic moduli
- Thermal expansion coefficients
- Fracture

Thermodynamic properties

- DU, DH, DS, DG, heat capacity
- Binding energies
- Solubility
- Melting temperature
- Vapor pressure
- Miscibility
- Phase diagrams
- Surface tension

Chemical properties

- Chemical reaction mechanisms and rates
- Reactivity on surfaces
- Solid-solid reactions
- Photochemical reactions

Transport properties

- Mass diffusion coefficient
- Permeability, diffusivity, solubility
- Thermal conductivity
- Viscosity
- Electrical conductivity

Electronic, optical, and magnetic properties

- Electron density distribution electrical moments
- Polarizabilities, hyperpolarizabilities
- Optical spectra
- Dielectric properties
- Piezoelectric properties
- Electrostatic potential
- Spin density distribution, magnetic moments
- Energy band structure metal, semiconductor, insulator
- Band gaps, band offsets at hetero-junctions
- Ionization energies and electron affinities
- Work function

Embrittlement of Cu Micro-Structures 5 µm



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Temperature dependent transition of intragranular plastic to intergranular brittle failure in electrodeposited Cu micro-tensile samples

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Keywords: Micromechanics Mechanical characterization Microanalysis Grain boundaries Fracture Plasticity ABSTRACT

Smaller grain sizes are known to improve the strength a Consequently, metallic thin films and structures which deposited under processing conditions that lead to a fi temperatures as low as 473 K the failure mode of 99.99 a ductile intragranular to brittle intergranular fracture. The strength and elongation to fracture. Chemical analyses impurities detected at grain boundaries. *In situ* microme microscope and atomistic simulations are performed to a



 Objective: Improve strength and ductility of Cu microstructures

MATERIAL

CrossMark

SCIENCE

- Approach: Introduce additives to reduce grain size (Hall-Petch effect)
- Challenge: Additives cause
 embrittlement at elevated temperatures

Sample Characterization



EBSD/ SEM



- (a, b, c) sample type A (medium grain size: $2.7 \pm 0.6 \mu$ m)
- (e, f, g) sample type B (medium grain size: $10.1 \pm 2.6 \mu$ m)

Stress-Strain Behavior



293 K: coarse-grained \rightarrow fine-grained

- yield stress and ultimate stress increase
- changes explained by Hall-Petch effect

473 K and 673 K:

- drastic reduction of elongation to fracture for fine-grained samples
- scattering of results for coarse-grained structures due to small number of grains

different additives in samples A and B!





Chemical Analysis



TOF-SIMS



- higher S, Cl content in fine-grained samples (additives)
- O, S, Cl enrichment at grain boundaries
- segregation of O, S, CI to grain boundaries and surfaces

Strategy of Atomistic Simulations



- Create models of surfaces and grain boundaries
- Understand grain boundary and surface segregation; compute segregation energies
- Understand grain boundary weakening due to S and CI; compute cleavage energies
- Find elements which could compensate the detrimental effect of S and CI but maintain the electronic and thermo-mechanical properties of Cu



Model of Grain Boundary

Σ5(001) Twist Grain Boundary





MedeA-Surface Builder MedeA-Interface Builder

Coincident Site Lattice Theory:

- minimize grain boundary energy
- maximize number of points common to original and rotated lattice

Grain Boundary and Surface



MedeA-Surface Builder, MedeA-Interface Builder



grain boundary segregation

surface segregation

- Understand grain boundary and surface segregation; compute segregation energies for $\Sigma5(001)$ and $\Sigma7(111)$ twisted grain boundaries
- Understand grain boundary weakening due to S and CI; compute cleavage energies
- Find elements which could compensate the detrimental effect of S and CI but maintain the electronic and thermo-mechanical properties of Cu

Grain-Boundary Segregation



Calculated energy release during segregation ΔE_{seg} of Cl and S in Cu.

	ΔE_{seg} [kJ/mol]	
	Cl	S
GB segregation, $\sum 5$ (001) surface segregation, (001) GB segregation, $\sum 7$ (111) surface segregation, (111)	- 69.9 - 321.5 - 53.5 - 272.0	- 54.3 - 145.3 - 56.3 - 129.9

S and CI have strong tendency to segregate from the bulk to the grain boundary

Tendency to segregate to the surface is even more pronounced

Grain-Boundary Cleavage



Calculated work of separation E_{sep} of $\sum 5$ and $\sum 7$ grain boundaries of pure Cu and Cu contaminated with Cl and S with planar impurity concentration c_{imp} in atoms per nm².

	<i>c_{imp}</i> [1/nm ²]	E_{sep} [J/m ²]		
		Pure Cu	Cl	S
∑5 (001) ∑7 (111)	0.77 0.62	1.08 1.13	0.82 0.89	1.01 1.04

• S impurities, and even more so, CI impurities cause pronounced reduction of the work of separation at the grain-boundaries



- Embrittlement caused by S and CI impurities
 - S and CI segregate from the bulk to the grain boundary
 - S and CI reduce the work of separation at the grain-boundaries
- Challenge: Find elements which compensate the detrimental effect of S and CI but maintain the electronic and thermomechanical properties of Cu

Grain boundaries Fracture Plasticity

Strength of Ni Grain Boundaries

- Which impurities are dangerous?
- Which alloying elements improve performance?





Low-Strain Cathode Materials for Solid-State Li-Ion Batteries

Li-Ion Battery









- Limited capacity: Li_xCoO_2 is unstable if more than half of Li is removed. In practice, operation is restricted to $0.5 \le x \le 1$; half of the capacity is not used.
- Li_xCoO₂ expands when Li is removed and contracts when Li is inserted. This causes degradation.
- The liquid electrolyte is flammable.
- Each cell behaves differently, which is a serious issue in battery packs.

Low-Strain Cathode Materials

Computational Design and Experimental Verification of Zero- and Low-strain Cathode Materials for Solid-State Li-ion batteries

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Volume change of electrodes on charge/discharge is major cause of degradation of Li-ion batteries
 stress generated at grain interfaces leads to destruction of solid-state batteries
 Use atomistic simulations to find high-voltage, zero-strain cathode materials for use with solid-state electrolytes

F. Rosciano et al., International Battery Association, Brisbane March 2014

Target and Optimization Strategy









M = Mg, V, Cr, Mn, Fe, Co, Ni, Cu, Al only configurations with three metals

- Use atomistic simulations to find high-voltage zero-strain cathode materials
 - Improve on spinel-type $\text{LiNi}_{0.5}\text{Mn}_{1.5}\text{O}_4$ ($\Delta V = 30 \text{ Å}^3$)
 - Start from LiMn₂O₄ and replace Mn

Optimization Strategy



• Start from pure compounds

- calculate volume for Li_xM₂O₄ with x=0,0.5,1 (M=Mg, Al, V, Cr, Mn, Fe, Co, Ni, Cu)
- Only Mg would allow for efficient volume change compensation
- Minimize volume change in threedimensional spaces spanned by three metals
- Choose three components:
 - Mn to provide structural stability
 - Mg to reduce volume change
 - Cr to compensate for electrochemical inactivity of Mg



F. Rosciano et al., patent 2014

Minimization of Volume Change



- Choose Mn, Mg, and Cr
- Mix according to three different principles
 - free optimization to obtain true zero-strain material
 - optimization constraining Mn content ≥ 0.1
 - optimization constraining Mg content ≤ 0.4



Calculated volume change for the optimized compositions

- Result
 - $LiMn_{0.14}Cr_{1.43}Mg_{0.43}O_4 \rightarrow \Delta V = 0 \text{ Å}^3$
 - $LiMn_{1.1}Cr_{0.5}Mg_{0.4}O_4 \rightarrow \Delta V = 3 \text{ Å}^3$
 - $LiMn_{0.59}Cr_{1.21}Mg_{0.2}O_4 \rightarrow \Delta V = 8 \text{ Å}^3$
 - LiMn_{1.5}Ni_{0.5}O₄ (benchmark) $\rightarrow \Delta V = 30 \text{ Å}^3$



F. Rosciano et al., Patent 2014

Synthesis and Characterization





$LiMn_{1.1}Cr_{0.5}Mg_{0.4}O_{4}$

- synthesized in mostly pure form (3% Li₂MnO₃ impurity phase)
- used to build electrochemical cells to study volume change on lithiation/delithiation
- ▶ measured volume change $\approx 4 \text{\AA}^3$
- first-charge curve shows reduced capacity as compared to benchmark LiNi_{0.5}Mn_{1.5}O₄

Patent



MedeA-VASP

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with international search report (Art. 21(3))

Microscopic Origin





- With increasing Li concentration
 - Mg-O bond lengths decrease, Mn-O bond lengths remain similar, Cr-O bond lengths increase
- Zero-strain behavior of Li₄Ti₅O₁₂ anode likewise based on balance of different local distortions



metal (e.g. W)

Effective Work Function in Gate Stacks

gate	metal	(e.g.	TiN)
-			

Si₃N₄

SiO₂/HfO₂

doped Si channel

Technology Issue



Metal Gate Electrode Impurity Engineering for Control of Effective Work Function

Jim Chambers, Hiro Niimi, Andrei Li-Fatou and Judy Shaw *Texas Instruments, Incorporated, Advanced CMOS*

Chris Hinkle, Jim Burris, Husam Alshareef, Richard Chapman, Rohit Galatage and Eric Vogel University of Texas at Dallas, Department of Materials Science and Engineering

Mikael Christensen, Clive Freeman and Erich Wimmer Materials Design, Incorporated



Problem



- Green electronics
 - How can one reduce the power consumption?

Complementary Metal Oxide Semiconductor



Next-Generation CMOS Devices





HfO₂/Ru/TaN gate stack

SiO₂ cannot be used at thicknesses less than 15 Å (leakage current is too high)

► HfO₂ replaces for SiO₂ as a dielectric

A critical design parameter is the work function of the metal. Which metallic material should be used so that it can be tuned for PMOS and NMOS devices?

Muhammad Mustafa Hussain ADVANCED FABRICATION PROCESSES FOR SUB-50 nm CMOS PhD thesis, University of Texas at Austin https://repositories.lib.utexas.edu/bitstream/handle/2152/2449/hussainm51214.pdf





Density of electronic states









Density of electronic states

Structure of the Interface





TiN Thin Film on HfO₂ Substrate materials design[®] MedeA-VASP TiN HfO₂ -15100 --15200 -15300 -15400 ≚ ш -15500 100 150 50 Step

Animation: see pptx slide

Electrostatic Potential at Interface



- Planar average exhibits ripples associated with each atomic layer
- Macroscopic average taken as the moving average across several layers
- Macroscopic average used as basis for comparison between test cases







MedeA-Interface Builder MedeA-VASP

- Experiments showed increase of EWF after annealing of stack under oxygen atmosphere
- Interpretation: oxygen inside TiN increases the work function

O replacing N in TiN cannot explain measured increase of EWF





materials design

- Interfacial O moves to HfO₂ to fill vacancies
- N builds up at interface
- ▶ O refills vacancies in TiN

- Dipole due to O replacing N screened in metallic TiN
- Dipole due to N replacing O at interface unscreened in dielectric HfO₂



MedeA-VASP

Thermodynamics of Vacancy Filling in TiN and HfO2



Vacancy filling by O highly favorable in both TiN and HfO₂



APPLIED PHYSICS LETTERS 96, 103502 (2010)

Interfacial oxygen and nitrogen induced dipole formation and vacancy passivation for increased effective work functions in TiN/HfO₂ gate stacks

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Effective work function (EWF) changes of TiN/HfO₂ annealed at low temperatures in different ambient environments are correlated with the atomic concentration of oxygen in the TiN near the metal/dielectric interface. EWF increases of 550 meV are achieved with anneals that incorporate oxygen throughout the TiN with $[O]=2.8 \times 10^{21}$ cm⁻³ near the TiN/HfO₂ interface. However, further increasing the oxygen concentration via more aggressive anneals results in a relative decrease of the EWF and increase in electrical thickness. First-principles calculations indicate the exchange of O and N atoms near the TiN/HfO₂ interface cause the formation of dipoles that increase the EWF. © 2010 American Institute of Physics. [doi:10.1063/1.3353993]

MedeA-Interface Builder MedeA-VASP

Complete Gate Stack Model





Composite Materials

AQUE POPULAIRE

debd

repo

NQU

BANQUE POPULAIR

В.

POP

Epoxy Thermosets

- Composites contain multiple components e.g. cured resins, coupling agents (primers), reinforcing particles or fibers. Properties of complex multiphase materials need to be studied.
- Example: Effect of primer concentration on mechanical properties
 - How much primer (coupling between SiO₂ surface and polymer) is optimal?

Epoxy-SiO₂: Model Building

Primed SiO₂+ unreacted epoxy, crosslinking and equilibration

MedeA-Amorphous Builder MedeA-Thermoset MedeA-LAMMPS

Epoxy-SiO₂: Mechanical Properties

Stiffness coefficient C_{33} for SiO₂ - epoxy composite layer systems with various levels of primer coverage:

MedeA-MT

Primed surface sites (%)	C ₃₃ (GPa)
0	7.2
12.5	7.8
25	8.8
50	5.0
Reference: Bulk Cured Resin	5.97 +/-0.29

Primer coverage at intermediate concentration produces optimal enhancement in small strain mechanical behavior

Fluids

0

Normal Boiling Point Temperature

MedeA-Gibbs

- Sample shown in the plot: 100 compounds
- Absolute average deviation of T_b calculated by GEMC simulation from the DIPPR* data is 1.4%.
- More than half of the compounds have an absolute deviation of T_b below 1.0%.

MedeA-GIBBS simulations (AUA & TraPPE-UA FF)

* Source experimental data: DIADEM: The DIPPR Information and Data Evaluation Manager for the Design Institute for Physical Properties, Version 6.0.0, Database 2011

Conclusion

- Atomic-scale modeling and simulations are becoming an integral part of industrial R&D
- Value
 - Predicting properties
 - Understanding mechanisms
- Examples
 - Stability of microstructures
 - Optimization of cathode materials
 - Control of effective work functions
 - Composites and Fluids
- Future trends: better coupling in multi-scale models: theoretical approaches, algorithms, software

- Driving innovation
- Creating valuable products
- Protecting the environment

Innovation by Smulation